Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006-3 (SOT883) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Leadless ultra small SMD package: 1.0 x 0.6 x 0.48 mm

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-410	mA
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 25 °C		-	1.2	1.4	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1	D I
2	S	source	2 🔲 📗 3	
3	D	drain	Transparent top view DFN1006-3 (SOT883)	G S S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMZ1200UPE	DFN1006-3	DFN1006-3: leadless ultra small plastic package; 3 solder lands	SOT883			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMZ1200UPE	ZL

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage	_		-8	8	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-410	mA
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-260	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-1.7	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	310	mW
			[1]	-	400	mW
		T _{sp} = 25 °C		-	1670	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode		1	,	,	
Is	source current	T _{amb} = 25 °C	[1]	-	-410	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

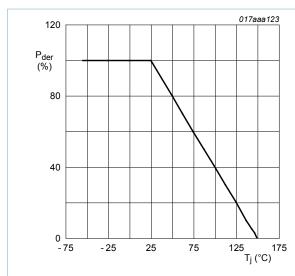


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

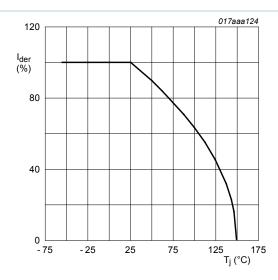


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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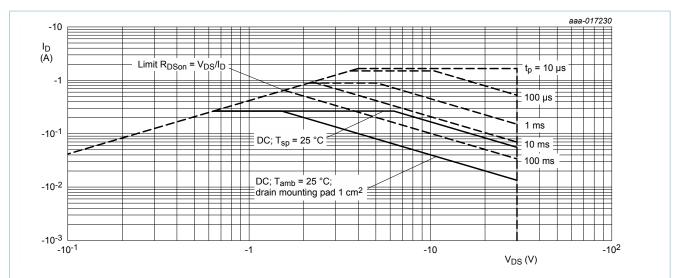


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fron	thermal resistance		[1]	-	350	405	K/W
	from junction to ambient		<u>[2]</u>	-	270	310	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	65	75	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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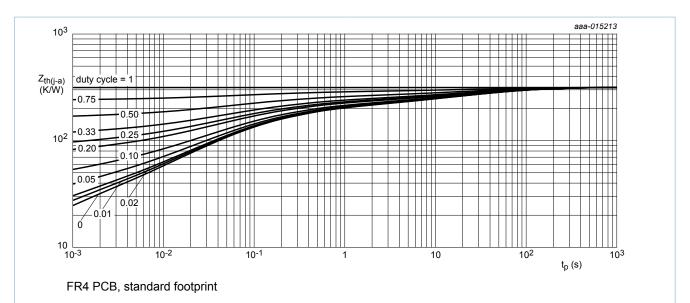
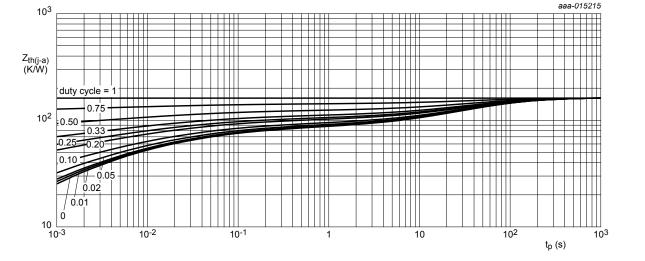


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-30	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
Doon	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -410 mA; T_j = 25 °C	-	1.2	1.4	Ω
		V _{GS} = -4.5 V; I _D = -410 mA; T _j = 150 °C	-	2	2.4	Ω
		V_{GS} = -2.5 V; I_D = -320 mA; T_j = 25 °C	-	1.7	2.3	Ω
		V_{GS} = -1.8 V; I_D = -80 mA; T_j = 25 °C	-	2.1	3.1	Ω
		V_{GS} = -1.5 V; I_D = -10 mA; T_j = 25 °C	-	3	5.1	Ω
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -410 mA; T_j = 25 °C	-	820	-	mS
Dynamic ch	naracteristics		1			
Q _{G(tot)}	total gate charge	V _{DS} = -15 V; I _D = -410 mA;	-	0.7	1.2	nC
Q_{GS}	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.2	-	nC
Q_{GD}	gate-drain charge		-	0.2	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	43.2	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	5.9	-	pF
C _{rss}	reverse transfer capacitance		-	4.2	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = -15 V; I _D = -410 mA;	-	3	-	ns
t _r	rise time	$V_{GS} = -4.5 \text{ V}; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	14	-	ns
t _f	fall time		-	5	-	ns
Source-drai	in diode		ı	1	1	1
V _{SD}	source-drain voltage	I_S = -410 mA; V_{GS} = 0 V; T_j = 25 °C	-	-0.95	-1.2	V
					1	

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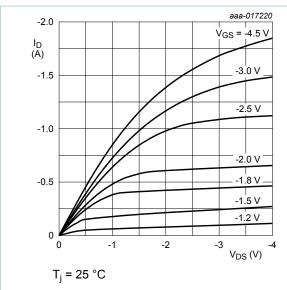
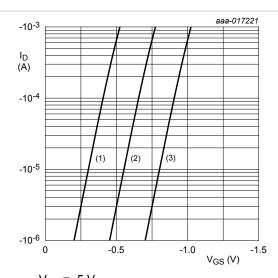


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



 $V_{DS} = -5 V$ $T_j = 25 °C$

(1) minimum values

(2) typical values

(3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage

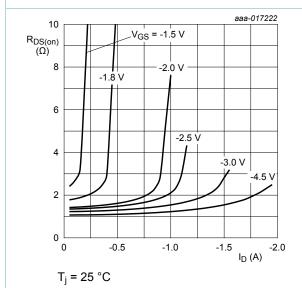


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

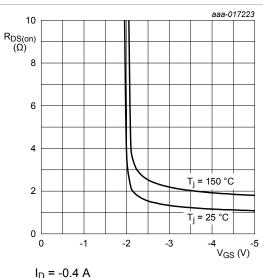


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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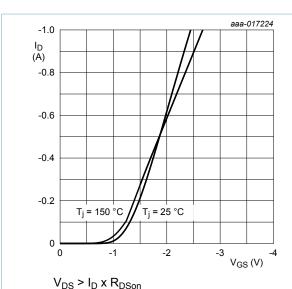


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

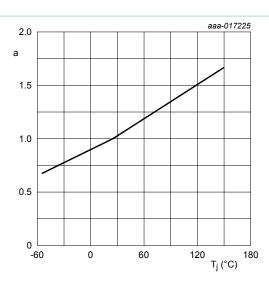
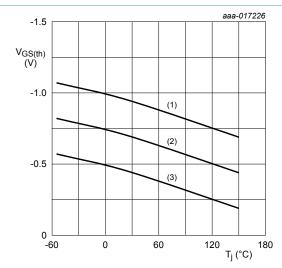


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

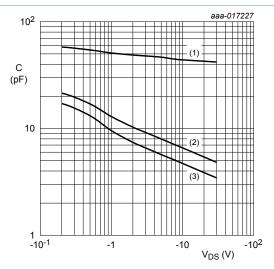
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = -250 \mu A; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature



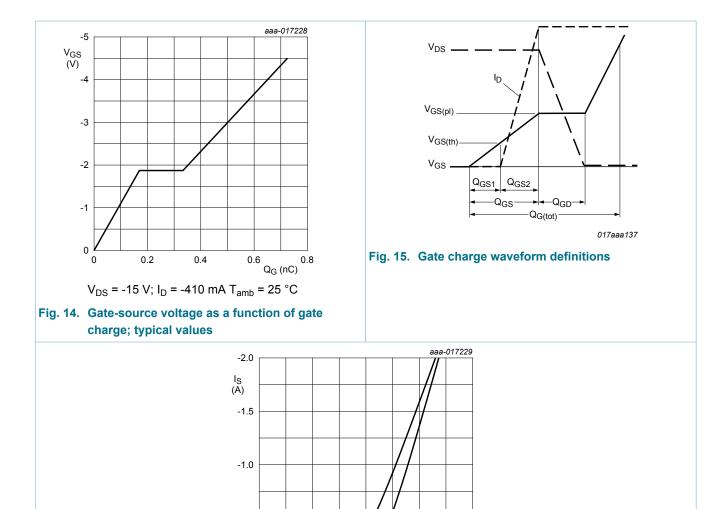
 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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T_j = 150 °C

-0.8

-0.4

T_j = 25 °C

-1.2 _{VSD} (V) -1.6

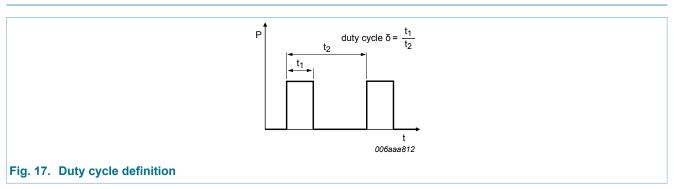
 $V_{GS} = 0 V$

Fig. 16. Source current as a function of source-drain voltage; typical values

-0.5

0

11. Test information



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12. Package outline

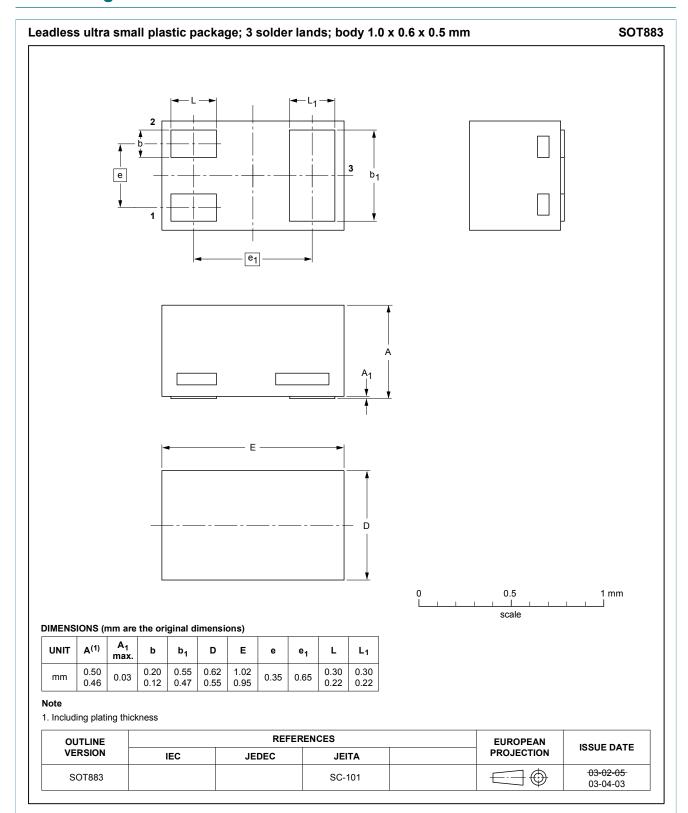


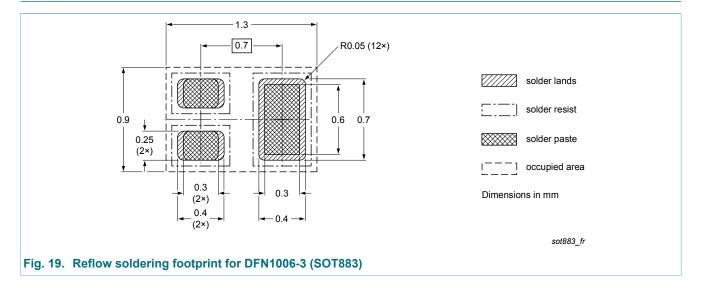
Fig. 18. Package outline DFN1006-3 (SOT883)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZ1200UPE v.1	20150325	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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